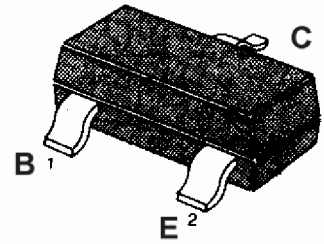


APPLICATION:High Frequency Amplifier Applications.

MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	35	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	I _C	50	mA
Collector Power Dissipation	P _C	100	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23


1.Base 2 .Emitter 3 .Collector

ELECTRICAL CHARACTERISTICS

(Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	40		240		V _{CE} = 12V, I _C = 2 mA
Collector Cut-off Current	I _{CB0}			0.1	μA	V _{CB} = 35V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} = 4 V, I _C =0
Collector-Base Breakdown Voltage	BV _{CB0}	35			V	I _C = 0.1 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	30			V	I _C = 1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	4			V	I _E = 0.1 mA, I _C =0
Base-Emitter Voltage	V _{BE}			1	V	I _C = 10 mA, I _B = 1 mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.4	V	I _C = 10 mA, I _B = 1 mA
Gain bandwidth product	f _T	100	300		MHz	I _C = 1 mA, V _{CE} = 10 V
Common Base Output Capacitance	C _{ob}		2	3.2	PF	V _{CB} = 10 V, I _E =0, f = 1 MHz
Power Gain	G _P	27	29	33	dB	V _{CE} = 6 V, I _C = 1 mA, f = 10.7 MHz

h_{FE} Classification And Marking

Print Mark	38R	38O	38Y
Classification	R	O	Y
h _{FE}	40~80	70~140	120~240